

isc Silicon PNP Power Transistor

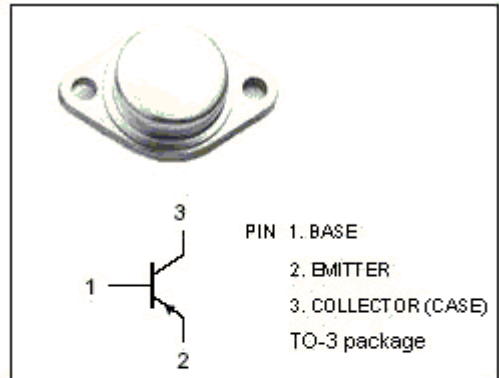
2SB634

DESCRIPTION

- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = -100V(\text{Min})$
- High Power Dissipation

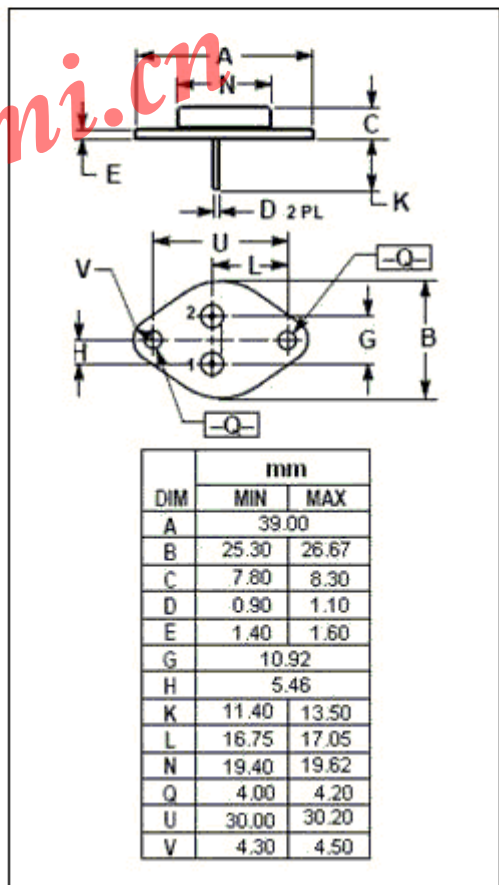
APPLICATIONS

- Designed for low frequency power amplifier applications.



ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-120	V
V_{CEO}	Collector-Emitter Voltage	-120	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current-Continuous	-7	A
I_{CM}	Collector Current-Peak	-10	A
P_C	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	60	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$



isc Silicon PNP Power Transistor

2SB634

ELECTRICAL CHARACTERISTICS

 $T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = -5\text{mA}; I_E = 0$	-120			V
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -50\text{mA}; R_{BE} = \infty$	-120			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = -5\text{mA}; I_C = 0$	-6			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -3\text{A}; I_B = -0.3\text{A}$			-1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB} = -80\text{V}; I_E = 0$			-0.1	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = -4\text{V}; I_C = 0$			-0.1	mA
h_{FE-1}	DC Current Gain	$I_C = -1\text{A}; V_{CE} = -5\text{V}$	40		320	
h_{FE-2}	DC Current Gain	$I_C = -3\text{A}; V_{CE} = -5\text{V}$	20			
f_T	Current-Gain—Bandwidth Product	$I_C = -1\text{A}; V_{CE} = -5\text{V}$		15		MHz

◆ h_{FE-1} Classifications

C	D	E	F
40-80	60-120	100-200	160-320